



Description

JMT N Enhancement Mode Power MOSFET

Features

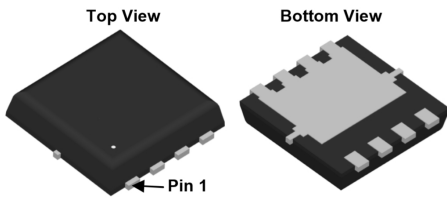
- 30V,12A
 $R_{DS(ON)} < 20m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 29m\Omega @ V_{GS} = 4.5V$
- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

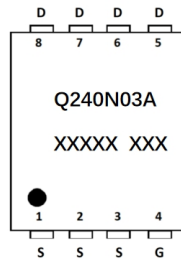
- Battery Protection
- Load Switch
- Power Management



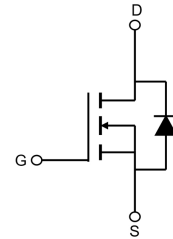
100% UIS TESTED!
100% ΔVds TESTED!



PDFN3.3X3.3-8L



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
Q240N03A	JMTQ240N03A	TAPING	PDFN3.3X3.3-8L	13inch	5000	50000

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units
V _{DSS}	Drain-Source Voltage	30	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current	T _C = 25°C	12
		T _C = 100°C	7.8
I _{DM}	Pulsed Drain Current ^{note1}	48	A
E _{AS}	Single Pulsed Avalanche Energy ^{note2}	11	mJ
P _D	Power Dissipation	T _C = 25°C	4.8
R _{θJC}	Thermal Resistance, Junction to Case	26	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note2</small>	V _{GS} =10V, I _D =5A	-	15	20	mΩ
		V _{GS} =4.5V, I _D =3A	-	21	29	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	490	-	pF
C _{oss}	Output Capacitance		-	79	-	pF
C _{rss}	Reverse Transfer Capacitance		-	61	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =5.8A, V _{GS} =10V	-	5.2	-	nC
Q _{gs}	Gate-Source Charge		-	0.9	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	1.3	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, I _D =3A, V _{GS} =10V, R _{REN} =3Ω	-	4.5	-	ns
t _r	Turn-on Rise Time		-	2.5	-	ns
t _{d(off)}	Turn-off Delay Time		-	14.5	-	ns
t _f	Turn-off Fall Time		-	3.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	12	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	48	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = 12A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25°C, V_{DD}=15V, V_G=10V, L=0.5mH, R_g=25Ω, I_{AS}=6.6A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure 1: Output Characteristics

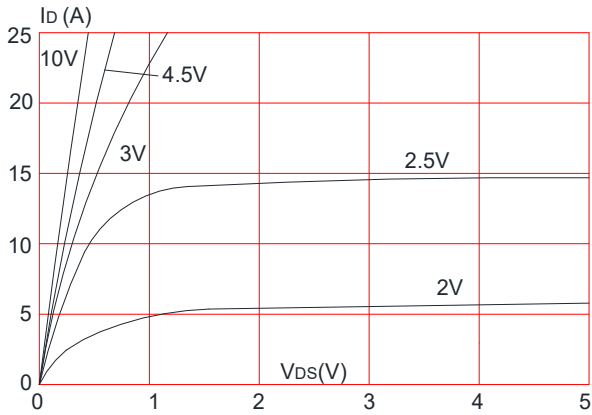


Figure 2: Typical Transfer Characteristics

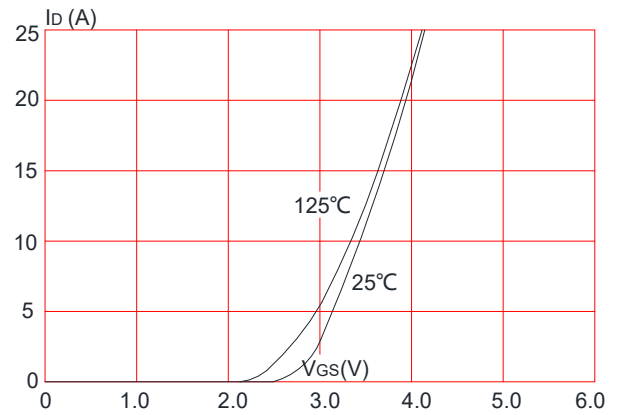


Figure 3: On-resistance vs. Drain Current

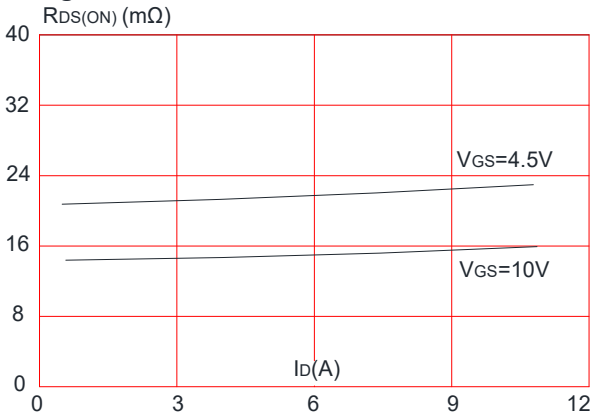


Figure 4: Body Diode Characteristics

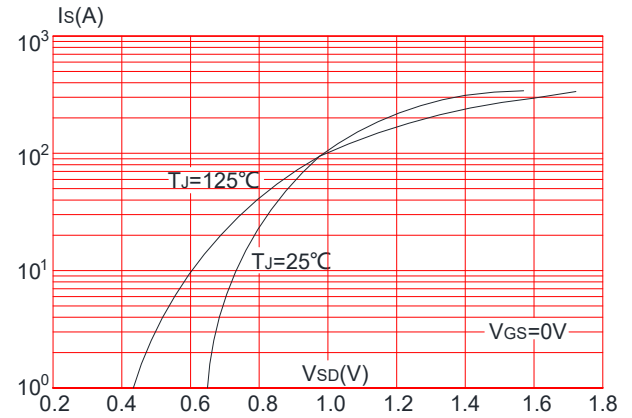


Figure 5: Gate Charge Characteristics

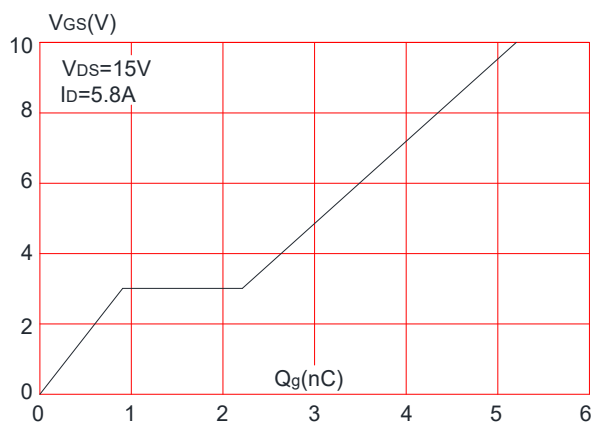


Figure 6: Capacitance Characteristics

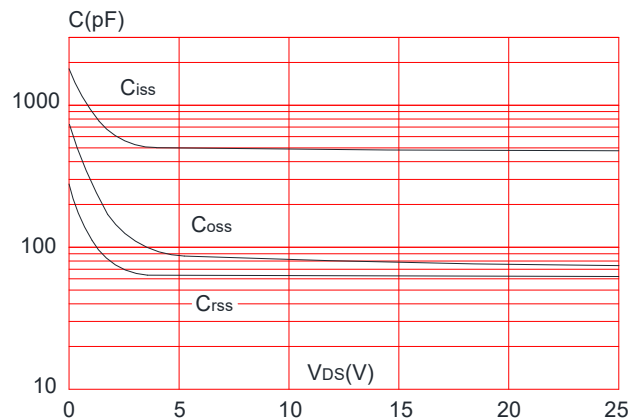




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

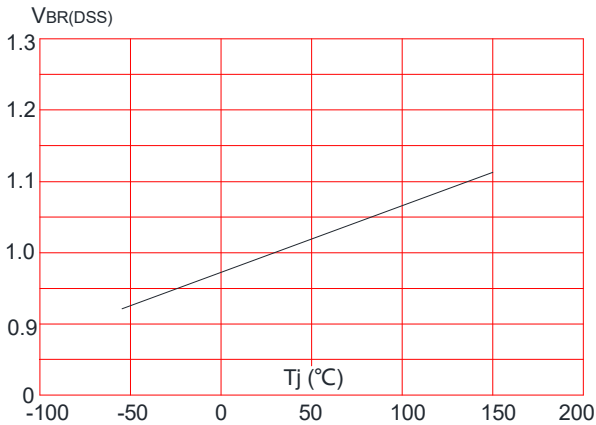


Figure 8: Normalized on Resistance vs. Junction Temperature

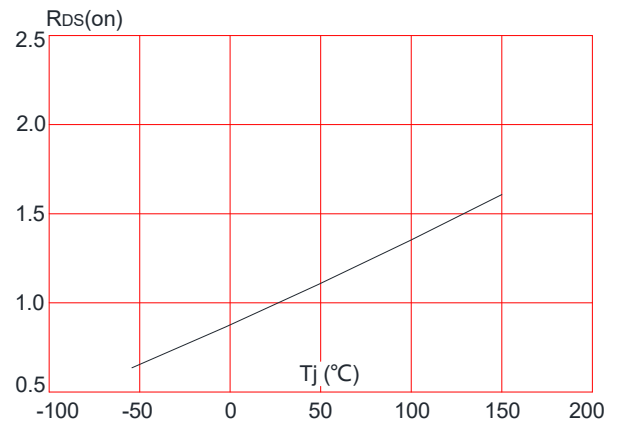


Figure 9: Maximum Safe Operating Area

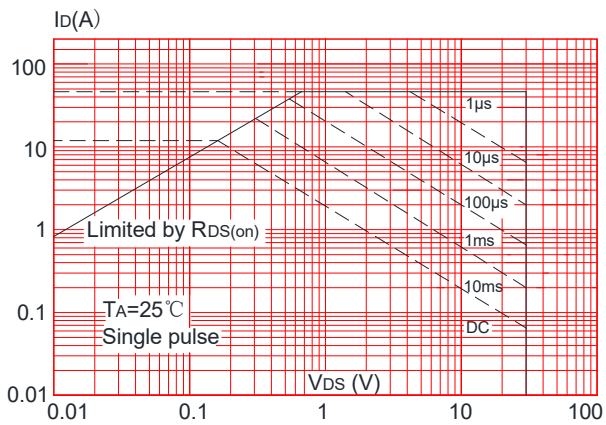


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

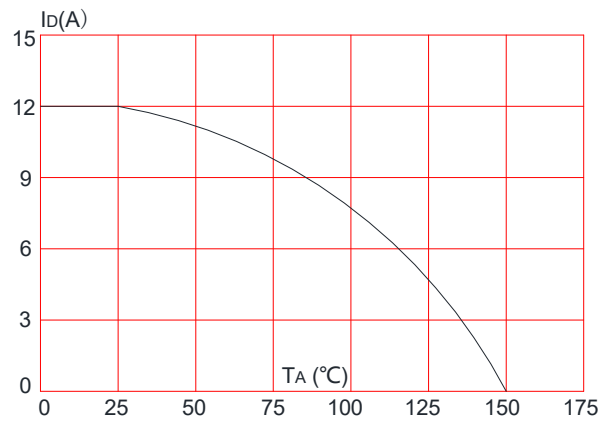
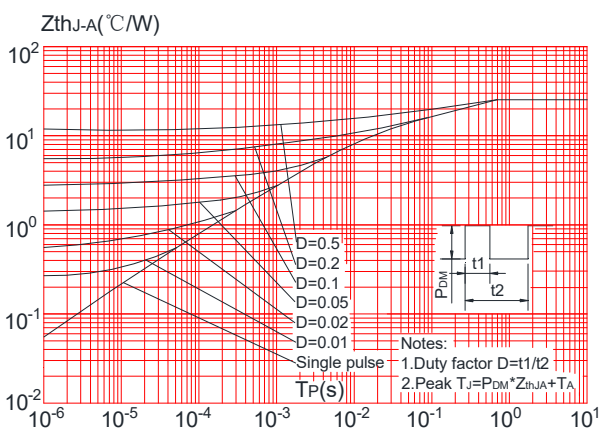


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit

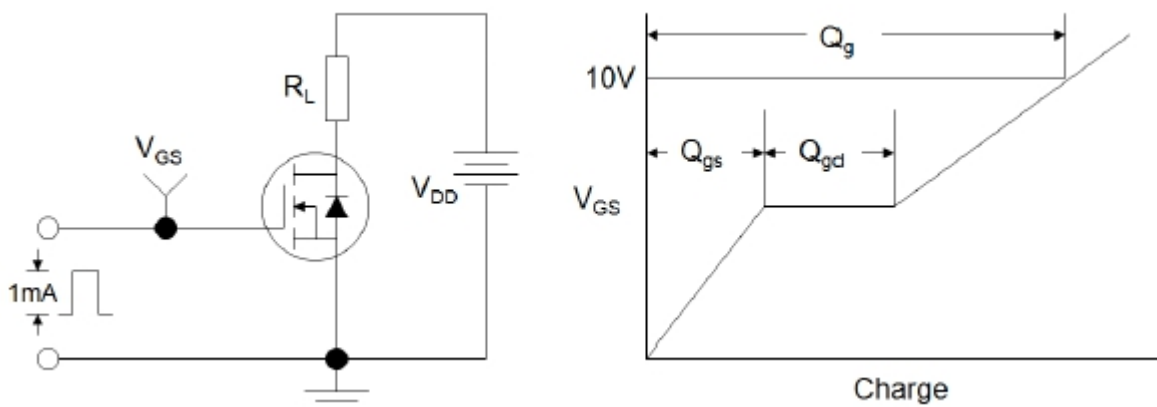


Figure1:Gate Charge Test Circuit & Waveform

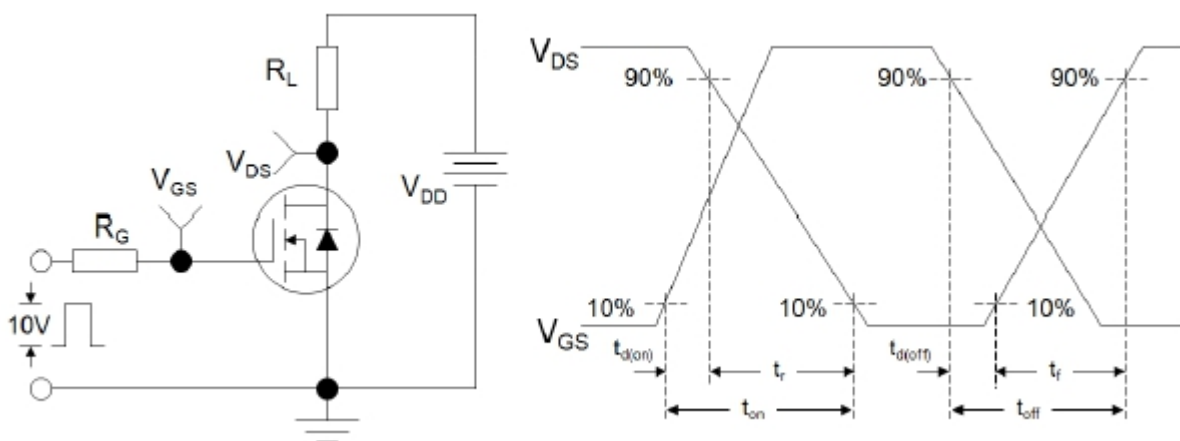


Figure 2: Resistive Switching Test Circuit & Waveforms

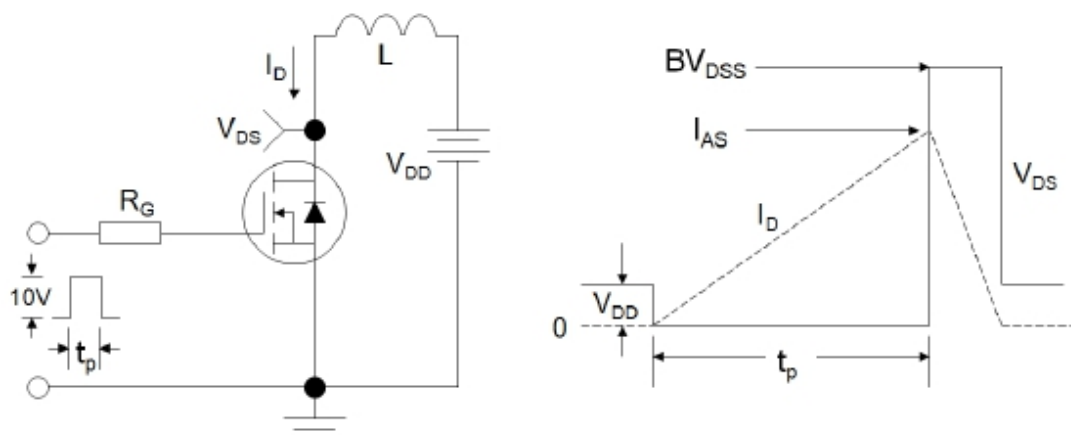
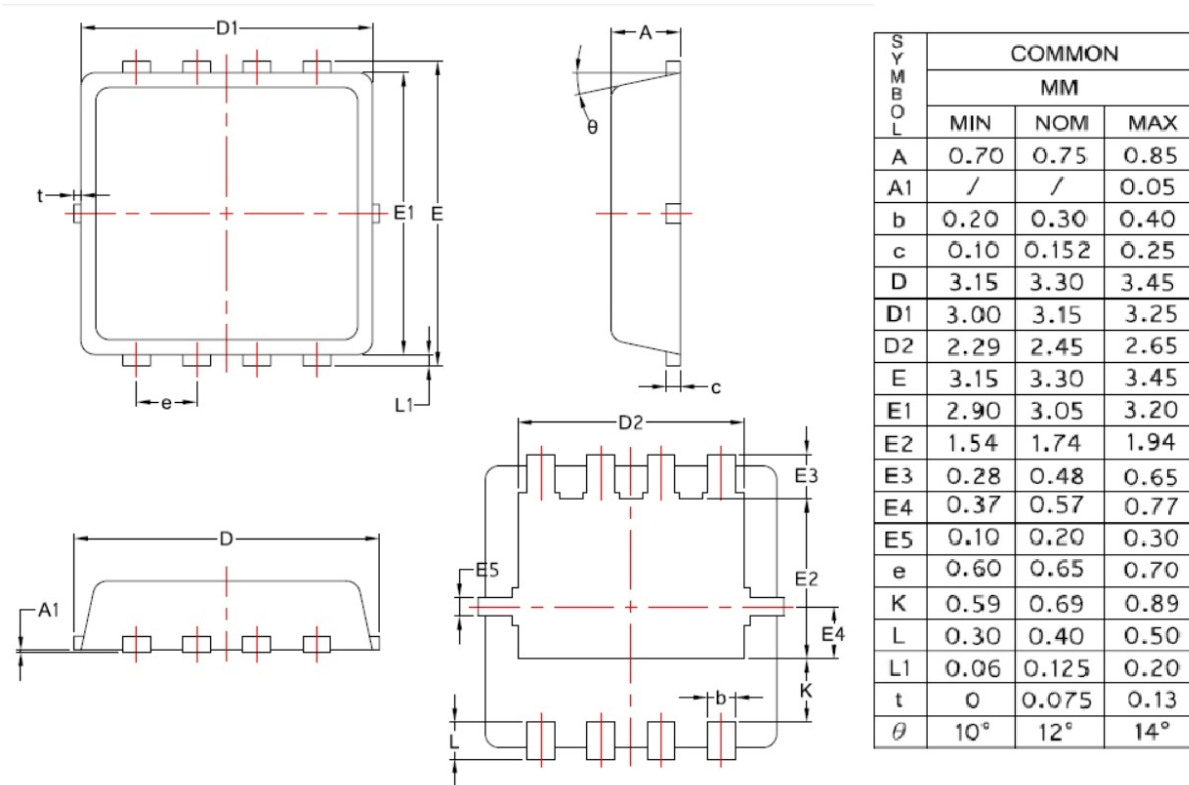


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



Package Mechanical Data-PDFN3.3X3.3-8L



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